74AUP1T34

Low-power dual supply translating buffer

Rev. 2 — 19 August 2010

Product data sheet

General description

The 74AUP1T34 provides a single buffer with two separate supply voltages. Input A is designed to track $V_{CC(A)}$. Output Y is designed to track $V_{CC(Y)}$. Both, $V_{CC(A)}$ and $V_{CC(Y)}$ accepts any supply voltage from 1.1 V to 3.6 V. This feature allows universal low voltage interfacing between any of the 1.2 V, 1.5 V, 1.8 V, 2.5 V, and 3.3 V voltage nodes.

Schmitt trigger action at all inputs makes the circuit tolerant to slower input rise and fall times across the entire V_{CC} range from 1.1 V to 3.6 V. This device ensures a very low static and dynamic power consumption across the entire V_{CC} range from 1.1 V to 3.6 V. This device is fully specified for partial power-down applications using I_{OFF} .

The I_{OFF} circuitry disables the output, preventing the damaging backflow current through the device when it is powered down.

2. Features and benefits

- Wide supply voltage range from 1.1 V to 3.6 V
- High noise immunity
- Complies with JEDEC standards:
 - ◆ JESD8-7 (1.2 V to 1.95 V)
 - ◆ JESD8-5 (1.8 V to 2.7 V)
 - ◆ JESD8-B (2.7 V to 3.6 V)
- ESD protection:
 - HBM JESD22-A114F Class 3A exceeds 5000 V
 - ◆ MM JESD22-A115-A exceeds 200 V
 - ◆ CDM JESD22-C101E exceeds 1000 V
- Wide supply voltage range:
 - ◆ V_{CC(A)}: 1.1 V to 3.6 V
 - ◆ V_{CC(Y)}: 1.1 V to 3.6 V
- Low static power consumption; I_{CC} = 0.9 μA (maximum)
- Each port operates over the full 1.1 V to 3.6 V power supply range
- Latch-up performance exceeds 100 mA per JESD 78 Class II
- Inputs accept voltages up to 3.6 V
- Low noise overshoot and undershoot < 10 % of V_{CC}
- I_{OFF} circuitry provides partial Power-down mode operation
- Multiple package options
- Specified from −40 °C to +85 °C and −40 °C to +125 °C



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3. Ordering information

Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
74AUP1T34GW	–40 °C to +125 °C	TSSOP5	plastic thin shrink small outline package; 5 leads; body width 1.25 mm	SOT353-1
74AUP1T34GM	–40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 \times 1.45 \times 0.5 mm	SOT886
74AUP1T34GF	–40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 \times 1 \times 0.5 mm	SOT891
74AUP1T34GN	–40 °C to +125 °C	XSON6	extremely thin small outline package; no leads; 6 terminals; body $0.9 \times 1.0 \times 0.35$ mm	SOT1115
74AUP1T34GS	–40 °C to +125 °C	XSON6	extremely thin small outline package; no leads; 6 terminals; body 1.0 \times 1.0 \times 0.35 mm	SOT1202

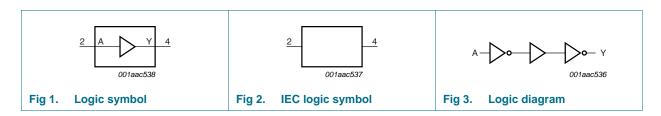
4. Marking

Table 2. Marking

9	
Type number	Marking code[1]
74AUP1T34GW	pQ
74AUP1T34GM	pQ
74AUP1T34GF	pQ
74AUP1T34GN	pQ
74AUP1T34GS	pQ

^[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

5. Functional diagram

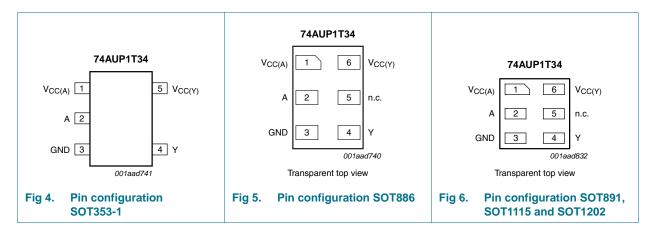


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6. Pinning information

6.1 Pinning



6.2 Pin description

Table 3. Pin description

Symbol	Pin		Description
	TSSOP5	XSON6	
$V_{CC(A)}$	1	1	supply voltage port A
A	2	2	data input A
GND	3	3	ground (0 V)
Υ	4	4	data output Y
n.c.	-	5	not connected
V _{CC(Y)}	5	6	supply voltage port Y

7. Functional description

Table 4. Function table[1]

Input	Output
A	Υ
L	L
Н	Н

[1] H = HIGH voltage level; L = LOW voltage level.

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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{CC(A)}$	supply voltage A		-0.5	+4.6	V
V _{CC(Y)}	supply voltage Y		-0.5	+4.6	V
I _{IK}	input clamping current	V _I < 0 V	-50	-	mA
VI	input voltage		<u>[1]</u> –0.5	+4.6	V
I _{OK}	output clamping current	V _O < 0 V	-50	-	mA
Vo	output voltage	Active mode and Power-down mode	<u>[1]</u> –0.5	+4.6	V
Io	output current	$V_O = 0 V \text{ to } V_{CC(Y)}$	-	±20	mA
I_{CC}	supply current		-	50	mA
I_{GND}	ground current		-50	-	mA
T _{stg}	storage temperature		-65	+150	°C
P _{tot}	total power dissipation	$T_{amb} = -40 ^{\circ}\text{C} \text{ to } +125 ^{\circ}\text{C}$	[2] _	250	mW

^[1] The minimum input and output voltage ratings may be exceeded if the input and output current ratings are observed.

^[2] For TSSOP5 packages: above 87.5 °C the value of P_{tot} derates linearly with 4.0 mW/K. For XSON6 packages: above 118 °C the value of P_{tot} derates linearly with 7.8 mW/K.

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9. Recommended operating conditions

Table 6. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{CC(A)}$	supply voltage A		1.1	3.6	V
$V_{CC(Y)}$	supply voltage Y		1.1	3.6	V
VI	input voltage		0	3.6	V
Vo	output voltage		0	$V_{CC(Y)}$	V
T_{amb}	ambient temperature		-40	+125	°C
Δt/ΔV	input transition rise and fall rate	control and data inputs; $V_{CC(A)} = 1.1 \text{ V to } 3.6 \text{ V}$	0	200	ns/V

10. Static characteristics

Table 7. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
T _{amb} = 2	5 °C					
V_{IH}	HIGH-level	$V_{CC(A)} = 1.1 \text{ V to } 1.95 \text{ V}; V_{CC(Y)} = 1.1 \text{ V to } 3.6 \text{ V}$	$0.65 \times V_{CC(A)}$	-	-	V
	input voltage	$V_{CC(A)} = 2.3 \text{ V to } 2.7 \text{ V}; V_{CC(Y)} = 1.1 \text{ V to } 3.6 \text{ V}$	1.6	-	-	V
		$V_{CC(A)} = 3.0 \text{ V to } 3.6 \text{ V}; V_{CC(Y)} = 1.1 \text{ V to } 3.6 \text{ V}$	2.0	-	-	V
V _{IL}	LOW-level input	$V_{CC(A)} = 1.1 \text{ V to } 1.95 \text{ V}; V_{CC(Y)} = 1.1 \text{ V to } 3.6 \text{ V}$	-	-	$0.35 \times V_{CC(A)}$	V
	voltage	$V_{CC(A)} = 2.3 \text{ V to } 2.7 \text{ V}; V_{CC(Y)} = 1.1 \text{ V to } 3.6 \text{ V}$	-	-	0.7	V
		$V_{CC(A)} = 3.0 \text{ V to } 3.6 \text{ V}; V_{CC(Y)} = 1.1 \text{ V to } 3.6 \text{ V}$	-	-	0.9	V
V _{OH}	HIGH-level	$V_I = V_{IH}$				
	output voltage	$I_O = -20 \mu A$; $V_{CC(A)} = V_{CC(Y)} = 1.1 \text{ V to } 3.6 \text{ V}$	$V_{CC(Y)} - 0.1$	-	-	V
		$I_{O} = -1.1 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 1.1 \text{ V}$	$0.75 \times V_{CC(Y)}$	-	-	V
		$I_{O} = -1.7 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 1.4 \text{ V}$	1.11	-	-	V
		$I_{O} = -1.9 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 1.65 \text{ V}$	1.32	-	-	V
		$I_{O} = -2.3 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 2.3 \text{ V}$	2.05	-	-	V
		$I_{O} = -3.1 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 2.3 \text{ V}$	1.9	-	-	V
		$I_{O} = -2.7 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 3.0 \text{ V}$	2.72	-	-	V
		$I_{O} = -4.0 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 3.0 \text{ V}$	2.6	-	-	V
V _{OL}	LOW-level	$V_I = V_{IL}$				
	output voltage	$I_O = 20 \mu A$; $V_{CC(A)} = V_{CC(Y)} = 1.1 \text{ V to } 3.6 \text{ V}$	-	-	0.1	V
		$I_O = 1.1 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 1.1 \text{ V}$	-	-	$0.3 \times V_{CC(Y)}$	V
		$I_O = 1.7 \text{ mA}$; $V_{CC(A)} = V_{CC(Y)} = 1.4 \text{ V}$	-	-	0.31	V
		$I_O = 1.9 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 1.65 \text{ V}$	-	-	0.31	V
		$I_{O} = 2.3 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 2.3 \text{ V}$	-	-	0.31	V
		$I_O = 3.1 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 2.3 \text{ V}$	-	-	0.44	V
		$I_O = 2.7 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 3.0 \text{ V}$	-	-	0.31	V
		$I_O = 4.0 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 3.0 \text{ V}$	-	-	0.44	V
lı	input leakage current	$V_{I} = 0 \text{ V to } 3.6 \text{ V}; V_{CC(A)} = V_{CC(Y)} = 1.1 \text{ V to } 3.6 \text{ V}$	-	-	±0.1	μА
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Table 7. Static characteristics ...continued
At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
l _{OFF}	power-off leakage current	A input; $V_1 = 0 \text{ V to } 3.6 \text{ V};$ $V_{CC(A)} = 0 \text{ V};$ $V_{CC(Y)} = 0 \text{ V to } 3.6 \text{ V}$	-	-	±0.2	μΑ
		Y output; V_O = 0 V to 3.6 V; $V_{CC(A)}$ = 0 V to 3.6 V; V_I = 0 V or 3.6 V; $V_{CC(Y)}$ = 0 V	-	-	±0.2	μΑ
ΔI_{OFF}	additional power-off	A input; $V_1 = 0 \text{ V to } 3.6 \text{ V}$; $V_{CC(A)} = 0 \text{ V to } 0.2 \text{ V}$; $V_{CC(Y)} = 0 \text{ V to } 3.6 \text{ V}$	-	-	±0.2	μΑ
	leakage current	Y output; $V_O = 0$ V to 3.6 V; $V_{CC(A)} = 0$ V to 3.6 V; $V_I = 0$ V or 3.6 V; $V_{CC(Y)} = 0$ V to 0.2 V	-	-	±0.2	μА
СС	supply current	port A; $V_I = GND$ or $V_{CC(A)}$; $I_O = 0$ A				
		$V_{CC(A)} = V_{CC(Y)} = 1.1 \text{ V to } 3.6 \text{ V}$	-	-	0.5	μΑ
		$V_{CC(A)} = 3.6 \text{ V}; V_{CC(Y)} = 0 \text{ V}$	-	-	0.5	μΑ
		$V_{CC(A)} = 0 \text{ V}; V_{CC(Y)} = 3.6 \text{ V}$	-	0.0	-	μΑ
		port Y; $V_I = GND$ or $V_{CC(A)}$; $I_O = 0$ A				
		$V_{CC(A)} = V_{CC(Y)} = 1.1 \text{ V to } 3.6 \text{ V}$	-	-	0.5	μΑ
		$V_{CC(A)} = 3.6 \text{ V}; V_{CC(Y)} = 0 \text{ V}$	-	0.0	-	μΑ
		$V_{CC(A)} = 0 \text{ V}; V_{CC(Y)} = 3.6 \text{ V}$	-	-	0.5	μΑ
		port A and port Y; V_I = GND or $V_{CC(A)}$; I_O = 0 A; $V_{CC(A)}$ = $V_{CC(Y)}$ = 1.1 V to 3.6 V	-	-	0.5	μΑ
Δl _{CC}	additional supply current	A input; $V_{CC(A)} = 3.3 \text{ V}$; $V_{CC(Y)} = 0 \text{ V}$ to 3.6 V; $V_I = V_{CC(A)} - 0.6 \text{ V}$	-	-	40	μΑ
Cı	input capacitance	A input; $V_{CC(A)} = V_{CC(Y)} = 0 \text{ V to } 3.6 \text{ V};$ $V_I = \text{GND or } V_{CC(A)}$	-	1.0	-	pF
Co	output capacitance	Y output; $V_O = GND$; $V_{CC(Y)} = 0 V$; $V_{CC(A)} = 0 V$ to 3.6 V	-	1.8	-	pF
T _{amb} = -	40 °C to +85 °C					
V _{IH}	HIGH-level	$V_{CC(A)} = 1.1 \text{ V to } 1.95 \text{ V; } V_{CC(Y)} = 1.1 \text{ V to } 3.6 \text{ V}$	$0.65 \times V_{CC(A)}$	-	-	V
	input voltage	$V_{CC(A)} = 2.3 \text{ V to } 2.7 \text{ V}; V_{CC(Y)} = 1.1 \text{ V to } 3.6 \text{ V}$	1.6	-	-	V
		$V_{CC(A)} = 3.0 \text{ V to } 3.6 \text{ V}; V_{CC(Y)} = 1.1 \text{ V to } 3.6 \text{ V}$	2.0	-	-	V
V _{IL}	LOW-level input	$V_{CC(A)} = 1.1 \text{ V to } 1.95 \text{ V}; V_{CC(Y)} = 1.1 \text{ V to } 3.6 \text{ V}$	-	-	$0.35 \times V_{CC(A)}$	V
	voltage	$V_{CC(A)} = 2.3 \text{ V to } 2.7 \text{ V}; V_{CC(Y)} = 1.1 \text{ V to } 3.6 \text{ V}$	-	-	0.7	V
		$V_{CC(A)} = 3.0 \text{ V to } 3.6 \text{ V}; V_{CC(Y)} = 1.1 \text{ V to } 3.6 \text{ V}$	-	-	0.9	V
V _{OH}	HIGH-level	$V_I = V_{IH}$				
	output voltage	$I_O = -20~\mu\text{A}$; $V_{CC(A)} = V_{CC(Y)} = 1.1~V$ to 3.6 V	$V_{CC(Y)} - 0.1$	-	-	V
		$I_O = -1.1 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 1.1 \text{ V}$	$0.7 \times V_{CC(Y)}$	-	-	V
		$I_O = -1.7 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 1.4 \text{ V}$	1.03	-	-	V
		$I_O = -1.9 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 1.65 \text{ V}$	1.30	-	-	V
		$I_O = -2.3 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 2.3 \text{ V}$	1.97	-	-	V
		$I_O = -3.1 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 2.3 \text{ V}$	1.85	-	-	V
		$I_{O} = -2.7 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 3.0 \text{ V}$	2.67	-	-	V
		$I_O = -4.0 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 3.0 \text{ V}$	2.55	-	-	V

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Table 7. Static characteristics ...continued
At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{OL}	LOW-level	$V_I = V_{IL}$				
	output voltage	$I_O = 20 \mu A$; $V_{CC(A)} = V_{CC(Y)} = 1.1 \text{ V to } 3.6 \text{ V}$	-	-	0.1	V
		$I_O = 1.1 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 1.1 \text{ V}$	-	-	$0.3 \times V_{CC(Y)}$	V
		$I_O = 1.7 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 1.4 \text{ V}$	-	-	0.37	V
		$I_O = 1.9 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 1.65 \text{ V}$	-	-	0.35	V
		$I_O = 2.3 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 2.3 \text{ V}$	-	-	0.33	V
		$I_O = 3.1 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 2.3 \text{ V}$	-	-	0.45	V
		$I_O = 2.7 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 3.0 \text{ V}$	-	-	0.33	V
		$I_O = 4.0 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 3.0 \text{ V}$	-	-	0.45	V
lı	input leakage current	$V_1 = 0 \text{ V to } 3.6 \text{ V}; V_{CC(A)} = V_{CC(Y)} = 1.1 \text{ V to } 3.6 \text{ V}$	-	-	±0.5	μА
I _{OFF}	power-off leakage current	A input; $V_I = 0 \text{ V to } 3.6 \text{ V}$; $V_{CC(A)} = 0 \text{ V}$; $V_{CC(Y)} = 0 \text{ V to } 3.6 \text{ V}$	-	-	±0.5	μА
		Y output; $V_O = 0$ V to 3.6 V; $V_{CC(A)} = 0$ V to 3.6 V; $V_I = 0$ V or 3.6 V; $V_{CC(Y)} = 0$ V	-	-	±0.5	μА
ΔI_{OFF}	additional power-off leakage current	A input; $V_I = 0 \text{ V to } 3.6 \text{ V};$ $V_{CC(A)} = 0 \text{ V to } 0.2 \text{ V};$ $V_{CC(Y)} = 0 \text{ V to } 3.6 \text{ V}$	-	-	±0.6	μΑ
		Y output; $V_0 = 0 \text{ V to } 3.6 \text{ V}; V_{CC(A)} = 0 \text{ V to } 3.6 \text{ V};$ $V_1 = 0 \text{ V or } 3.6 \text{ V}; V_{CC(Y)} = 0 \text{ V to } 0.2 \text{ V}$	-	-	±0.6	μΑ
I _{CC}	supply current	port A; $V_I = GND$ or $V_{CC(A)}$; $I_O = 0$ A				
		$V_{CC(A)} = V_{CC(Y)} = 1.1 \text{ V to } 3.6 \text{ V}$	-	-	0.9	μΑ
		$V_{CC(A)} = 3.6 \text{ V}; V_{CC(Y)} = 0 \text{ V}$	-	-	0.9	μΑ
		$V_{CC(A)} = 0 \text{ V}; V_{CC(Y)} = 3.6 \text{ V}$	-	0.0	-	μΑ
		port Y; $V_I = GND$ or $V_{CC(A)}$; $I_O = 0$ A				
		$V_{CC(A)} = V_{CC(Y)} = 1.1 \text{ V to } 3.6 \text{ V}$	-	-	0.9	μΑ
		$V_{CC(A)} = 3.6 \text{ V}; V_{CC(Y)} = 0 \text{ V}$	-	0.0	-	μΑ
		$V_{CC(A)} = 0 \text{ V}; V_{CC(Y)} = 3.6 \text{ V}$	-	-	0.9	μΑ
		port A and port Y; V_I = GND or $V_{CC(A)}$; I_O = 0 A; $V_{CC(A)}$ = $V_{CC(Y)}$ = 1.1 V to 3.6 V	-	-	0.9	μА
Δl _{CC}	additional supply current	A input; $V_{CC(A)} = 3.3 \text{ V}$; $V_{CC(Y)} = 0 \text{ V}$ to 3.6 V; $V_I = V_{CC(A)} - 0.6 \text{ V}$	-	-	50	μΑ
T _{amb} = -	40 °C to +125 °C					
V _{IH}	HIGH-level	$V_{CC(A)} = 1.1 \text{ V to } 1.95 \text{ V}; V_{CC(Y)} = 1.1 \text{ V to } 3.6 \text{ V}$	$0.7 \times V_{CC(A)}$	-	-	V
	input voltage	$V_{CC(A)} = 2.3 \text{ V to } 2.7 \text{ V}; V_{CC(Y)} = 1.1 \text{ V to } 3.6 \text{ V}$	1.6	-	-	V
		$V_{CC(A)} = 3.0 \text{ V to } 3.6 \text{ V}; V_{CC(Y)} = 1.1 \text{ V to } 3.6 \text{ V}$	2.0	-	-	V
V _{IL}	LOW-level input	$V_{CC(A)} = 1.1 \text{ V to } 1.95 \text{ V}; V_{CC(Y)} = 1.1 \text{ V to } 3.6 \text{ V}$	-	-	$0.3 \times V_{CC(A)}$	V
	voltage	$V_{CC(A)} = 2.3 \text{ V to } 2.7 \text{ V}; V_{CC(Y)} = 1.1 \text{ V to } 3.6 \text{ V}$	-	-	0.7	٧
		$V_{CC(A)} = 3.0 \text{ V to } 3.6 \text{ V}; V_{CC(Y)} = 1.1 \text{ V to } 3.6 \text{ V}$	-	-	0.9	V

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Table 7. Static characteristics ...continued
At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{OH}	HIGH-level	$V_I = V_{IH}$				
	output voltage	$I_O = -20 \mu A$; $V_{CC(A)} = V_{CC(Y)} = 1.1 \text{ V to } 3.6 \text{ V}$	V _{CC(Y)} - 0.11	-	-	V
		$I_{O} = -1.1 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 1.1 \text{ V}$	$0.6 \times V_{CC(Y)}$	-	-	V
		$I_{O} = -1.7 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 1.4 \text{ V}$	0.93	-	-	V
		$I_{O} = -1.9 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 1.65 \text{ V}$	1.17	-	-	V
		$I_{O} = -2.3 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 2.3 \text{ V}$	1.77	-	-	V
		$I_O = -3.1 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 2.3 \text{ V}$	1.67	-	-	V
		$I_{O} = -2.7 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 3.0 \text{ V}$	2.40	-	-	V
		$I_{O} = -4.0 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 3.0 \text{ V}$	2.30	-	-	V
V _{OL}	LOW-level	$V_I = V_{IL}$				
	output voltage	$I_O = 20 \mu A$; $V_{CC(A)} = V_{CC(Y)} = 1.1 \text{ V to } 3.6 \text{ V}$	-	-	0.11	V
		$I_O = 1.1 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 1.1 \text{ V}$	-	-	$0.33 \times V_{CC(Y)}$	V
		$I_O = 1.7 \text{ mA}$; $V_{CC(A)} = V_{CC(Y)} = 1.4 \text{ V}$	-	-	0.41	V
		$I_O = 1.9 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 1.65 \text{ V}$	-	-	0.39	V
		$I_{O} = 2.3 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 2.3 \text{ V}$	-	-	0.36	V
		$I_O = 3.1 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 2.3 \text{ V}$	-	-	0.50	V
		$I_{O} = 2.7 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 3.0 \text{ V}$	-	-	0.36	V
		$I_O = 4.0 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 3.0 \text{ V}$	-	-	0.50	V
l _l	input leakage current	$V_I = 0 \text{ V to } 3.6 \text{ V}; V_{CC(A)} = V_{CC(Y)} = 1.1 \text{ V to } 3.6 \text{ V}$	-	-	±0.75	μΑ
I _{OFF}	power-off leakage current	A input; $V_1 = 0 \text{ V to } 3.6 \text{ V}$; $V_{CC(A)} = 0 \text{ V}$; $V_{CC(Y)} = 0 \text{ V to } 3.6 \text{ V}$	-	-	±0.75	μΑ
	Ç	Y output; $V_O = 0 \text{ V to } 3.6 \text{ V}; V_{CC(A)} = 0 \text{ V to } 3.6 \text{ V}; V_I = 0 \text{ V or } 3.6 \text{ V}; V_{CC(Y)} = 0 \text{ V}$	-	-	±0.75	μΑ
Δl _{OFF}	additional power-off	A input; $V_I = 0 \text{ V to } 3.6 \text{ V};$ $V_{CC(A)} = 0 \text{ V to } 0.2 \text{ V};$ $V_{CC(Y)} = 0 \text{ V to } 3.6 \text{ V}$	-	-	±0.75	μΑ
	leakage current	Y output; $V_O = 0 \text{ V to } 3.6 \text{ V}; V_{CC(A)} = 0 \text{ V to } 3.6 \text{ V}; V_I = 0 \text{ V or } 3.6 \text{ V}; V_{CC(Y)} = 0 \text{ V to } 0.2 \text{ V}$	-	-	±0.75	μΑ
Icc	supply current	port A; $V_I = GND$ or $V_{CC(A)}$; $I_O = 0$ A				
		$V_{CC(A)} = V_{CC(Y)} = 1.1 \text{ V to } 3.6 \text{ V}$	-	-	1.4	μΑ
		$V_{CC(A)} = 3.6 \text{ V}; V_{CC(Y)} = 0 \text{ V}$	-	-	1.4	μΑ
		$V_{CC(A)} = 0 \text{ V}; V_{CC(Y)} = 3.6 \text{ V}$	-	0.0	-	μΑ
		port Y; $V_I = GND$ or $V_{CC(A)}$; $I_O = 0$ A				
		$V_{CC(A)} = V_{CC(Y)} = 1.1 \text{ V to } 3.6 \text{ V}$	-	-	1.4	μΑ
		$V_{CC(A)} = 3.6 \text{ V}; V_{CC(Y)} = 0 \text{ V}$	-	0.0	-	μΑ
		$V_{CC(A)} = 0 \text{ V}; V_{CC(Y)} = 3.6 \text{ V}$	-	-	1.4	μΑ
		port A and port Y; V_I = GND or $V_{CC(A)}$; I_O = 0 A; $V_{CC(A)}$ = $V_{CC(Y)}$ = 1.1 V to 3.6 V	-	-	1.4	μΑ
ΔI_{CC}	additional supply current	A input; $V_{CC(A)} = 3.3 \text{ V}$; $V_{CC(Y)} = 0 \text{ V}$ to 3.6 V; $V_{I} = V_{CC(A)} - 0.6 \text{ V}$	-	-	75	μА

Low-power dual supply translating buffer

11. Dynamic characteristics

Table 8. Dynamic characteristicsVoltages are referenced to GND (ground = 0 V); for test circuit see Figure 8.

	Parameter	Conditions			25 °C		-40 °C to +125 °C			
				Min	Typ[1]	Max	Min	Max (85 °C)	Max (125 °C)	
C _L = 5 p	F; V _{CC(A)} = 1.1 V to	1.3 V			'	•		'	'	
t _{pd}	propagation delay	A to Y; see Figure 7	[2]							
		$V_{CC(Y)} = 1.1 \text{ V to } 1.3 \text{ V}$		2.6	9.8	25.4	2.3	25.9	25.9	ns
		$V_{CC(Y)} = 1.4 \text{ V to } 1.6 \text{ V}$		2.4	7.1	15.3	2.2	16.3	16.7	ns
		$V_{CC(Y)} = 1.65 \text{ V to } 1.95 \text{ V}$		2.1	6.0	12.7	1.9	13.8	14.3	ns
		$V_{CC(Y)} = 2.3 \text{ V to } 2.7 \text{ V}$		2.0	5.1	9.8	2.0	10.5	10.9	ns
		$V_{CC(Y)} = 3.0 \text{ V to } 3.6 \text{ V}$		2.1	4.7	8.8	1.9	9.1	9.3	ns
C _L = 5 p	F; V _{CC(A)} = 1.4 V to	1.6 V								
t _{pd}	propagation delay	A to Y; see Figure 7	[2]							
		$V_{CC(Y)} = 1.1 \text{ V to } 1.3 \text{ V}$		2.3	9.1	23.9	2.0	24.5	24.5	ns
		$V_{CC(Y)} = 1.4 \text{ V to } 1.6 \text{ V}$		2.1	6.4	13.6	1.9	14.7	15.2	ns
		$V_{CC(Y)} = 1.65 \text{ V to } 1.95 \text{ V}$		1.8	5.3	10.9	1.6	12.1	12.6	ns
		$V_{CC(Y)} = 2.3 \text{ V to } 2.7 \text{ V}$		1.7	4.3	7.8	1.6	8.7	9.2	ns
		$V_{CC(Y)} = 3.0 \text{ V to } 3.6 \text{ V}$		1.8	3.9	6.6	1.6	7.1	7.5	ns
C _L = 5 p	F; V _{CC(A)} = 1.65 V to	1.95 V								
t _{pd}	propagation delay	A to Y; see Figure 7	[2]							
		$V_{CC(Y)} = 1.1 \text{ V to } 1.3 \text{ V}$		2.2	8.8	23.2	1.9	23.9	24.0	ns
		$V_{CC(Y)} = 1.4 \text{ V to } 1.6 \text{ V}$		2.0	6.0	13.0	1.8	14.1	14.6	ns
		$V_{CC(Y)} = 1.65 \text{ V to } 1.95 \text{ V}$		1.8	4.9	10.3	1.5	11.4	12.0	ns
		$V_{CC(Y)} = 2.3 \text{ V to } 2.7 \text{ V}$		1.6	3.9	7.2	1.5	8.0	8.5	ns
		$V_{CC(Y)} = 3.0 \text{ V to } 3.6 \text{ V}$		1.7	3.5	5.9	1.5	6.4	6.8	ns
C _L = 5 p	F; V _{CC(A)} = 2.3 V to	2.7 V								
t _{pd}	propagation delay	A to Y; see Figure 7	[2]							
		$V_{CC(Y)} = 1.1 \text{ V to } 1.3 \text{ V}$		2.2	8.4	22.8	1.9	23.4	23.4	ns
		$V_{CC(Y)} = 1.4 \text{ V to } 1.6 \text{ V}$		1.9	5.7	12.3	1.8	13.4	14.0	ns
		$V_{CC(Y)} = 1.65 \text{ V to } 1.95 \text{ V}$		1.7	4.6	9.6	1.5	10.7	11.2	ns
		$V_{CC(Y)} = 2.3 \text{ V to } 2.7 \text{ V}$		1.5	3.5	6.3	1.5	7.2	7.7	ns
		$V_{CC(Y)} = 3.0 \text{ V to } 3.6 \text{ V}$		1.6	3.1	5.1	1.4	5.6	6.0	ns
C _L = 5 p	F; V _{CC(A)} = 3.0 V to	3.6 V								
t _{pd}	propagation delay	A to Y; see Figure 7	[2]							
		$V_{CC(Y)} = 1.1 \text{ V to } 1.3 \text{ V}$		2.2	8.1	22.5	1.9	22.9	22.9	ns
		$V_{CC(Y)} = 1.4 \text{ V to } 1.6 \text{ V}$		1.9	5.4	12.0	1.8	12.9	13.4	ns
		$V_{CC(Y)} = 1.65 \text{ V to } 1.95 \text{ V}$		1.7	4.3	9.2	1.5	10.2	10.7	ns
		$V_{CC(Y)} = 2.3 \text{ V to } 2.7 \text{ V}$		1.5	3.3	6.0	1.5	6.7	7.2	ns
		$V_{CC(Y)} = 3.0 \text{ V to } 3.6 \text{ V}$		1.6	2.9	4.8	1.4	5.2	5.5	ns

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Low-power dual supply translating buffer

Table 8. Dynamic characteristics ...continued

Voltages are referenced to GND (ground = 0 V); for test circuit see <u>Figure 8</u>.

Symbol	Parameter	Conditions		25 °C		-40	–40 °C to +125 °C			
				Min	Typ[1]	Max	Min	Max (85 °C)	Max (125 °C)	
C _L = 10 p	$oF; V_{CC(A)} = 1.1 V to$	1.3 V			'		,			
t_{pd}	propagation delay	A to Y; see Figure 7	[2]							
		$V_{CC(Y)} = 1.1 \text{ V to } 1.3 \text{ V}$		2.6	10.7	27.1	2.5	27.6	27.6	ns
		$V_{CC(Y)} = 1.4 \text{ V to } 1.6 \text{ V}$		2.6	7.7	16.7	2.3	17.5	17.6	ns
		$V_{CC(Y)} = 1.65 \text{ V to } 1.95 \text{ V}$		2.7	6.6	13.4	2.4	14.2	14.7	ns
		$V_{CC(Y)} = 2.3 \text{ V to } 2.7 \text{ V}$		2.2	5.6	10.3	2.2	11.0	11.4	ns
		$V_{CC(Y)} = 3.0 \text{ V to } 3.6 \text{ V}$		2.5	5.3	9.5	2.2	9.7	10.0	ns
C _L = 10 p	oF; V _{CC(A)} = 1.4 V to	1.6 V								
t _{pd}	propagation delay	A to Y; see Figure 7	[2]							
		V _{CC(Y)} = 1.1 V to 1.3 V		2.4	10.0	25.6	2.2	26.1	26.1	ns
		V _{CC(Y)} = 1.4 V to 1.6 V		2.4	7.0	15.0	2.0	15.8	16.4	ns
		$V_{CC(Y)} = 1.65 \text{ V to } 1.95 \text{ V}$		2.4	5.9	11.6	2.1	12.5	13.1	ns
		$V_{CC(Y)} = 2.3 \text{ V to } 2.7 \text{ V}$		2.0	4.8	8.4	1.9	9.2	9.7	ns
		$V_{CC(Y)} = 3.0 \text{ V to } 3.6 \text{ V}$		2.2	4.4	7.4	1.9	7.7	8.1	ns
C _L = 10 p	oF; V _{CC(A)} = 1.65 V t	o 1.95 V								
t _{pd}	propagation delay	A to Y; see Figure 7								
		V _{CC(Y)} = 1.1 V to 1.3 V		2.3	9.7	24.8	2.1	25.5	25.7	ns
		$V_{CC(Y)} = 1.4 \text{ V to } 1.6 \text{ V}$		2.3	6.6	14.3	2.0	15.3	15.8	ns
		$V_{CC(Y)} = 1.65 \text{ V to } 1.95 \text{ V}$		2.3	5.5	11.0	2.0	11.9	12.5	ns
		$V_{CC(Y)} = 2.3 \text{ V to } 2.7 \text{ V}$		1.9	4.4	7.7	1.8	8.6	9.0	ns
		$V_{CC(Y)} = 3.0 \text{ V to } 3.6 \text{ V}$		2.1	4.0	6.6	1.8	7.1	7.4	ns
C _L = 10 p	oF; V _{CC(A)} = 2.3 V to	2.7 V								
t _{pd}	propagation delay	A to Y; see Figure 7	[2]							
		V _{CC(Y)} = 1.1 V to 1.3 V		2.3	9.3	24.4	2.1	25.1	25.1	ns
		$V_{CC(Y)} = 1.4 \text{ V to } 1.6 \text{ V}$		2.2	6.3	13.6	1.9	14.6	15.1	ns
		$V_{CC(Y)} = 1.65 \text{ V to } 1.95 \text{ V}$		2.2	5.1	10.3	2.0	11.2	11.7	ns
		$V_{CC(Y)} = 2.3 \text{ V to } 2.7 \text{ V}$		1.8	4.1	6.9	1.8	7.7	8.2	ns
		$V_{CC(Y)} = 3.0 \text{ V to } 3.6 \text{ V}$		2.0	3.6	5.8	1.7	6.3	6.6	ns
C _L = 10 p	oF; V _{CC(A)} = 3.0 V to	3.6 V								
t _{pd}	propagation delay	A to Y; see Figure 7	[2]							
		$V_{CC(Y)} = 1.1 \text{ V to } 1.3 \text{ V}$		2.3	9.0	24.2	2.1	24.6	24.6	ns
		$V_{CC(Y)} = 1.4 \text{ V to } 1.6 \text{ V}$		2.2	6.0	13.3	1.9	14.1	14.6	ns
		$V_{CC(Y)} = 1.65 \text{ V to } 1.95 \text{ V}$		2.2	4.9	9.9	2.0	10.6	11.2	ns
		$V_{CC(Y)} = 2.3 \text{ V to } 2.7 \text{ V}$		1.8	3.9	6.5	1.8	7.3	7.7	ns
		$V_{CC(Y)} = 3.0 \text{ V to } 3.6 \text{ V}$		2.0	3.5	5.4	1.7	5.8	6.2	ns

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Low-power dual supply translating buffer

Table 8. Dynamic characteristics ...continued Voltages are referenced to GND (ground = 0 V); for test circuit see <u>Figure 8</u>.

Symbol	Parameter	Conditions			25 °C		-40 °C to +125 °C			Unit
				Min	Typ[1]	Max	Min	Max (85 °C)	Max (125 °C)	
C _L = 15	pF; V _{CC(A)} = 1.1 V to	1.3 V			'	'		'	'	
t _{pd}	propagation delay	A to Y; see Figure 7	[2]							
		V _{CC(Y)} = 1.1 V to 1.3 V		3.0	11.5	28.6	2.8	29.2	29.2	ns
		V _{CC(Y)} = 1.4 V to 1.6 V		3.1	8.3	17.3	2.7	18.6	19.1	ns
		V _{CC(Y)} = 1.65 V to 1.95 V		2.8	7.1	14.1	2.7	15.2	15.8	ns
		$V_{CC(Y)} = 2.3 \text{ V to } 2.7 \text{ V}$		2.6	6.1	11.1	2.7	11.6	12.1	ns
		V _{CC(Y)} = 3.0 V to 3.6 V		2.9	5.7	9.9	2.6	10.3	10.6	ns
C _L = 15	pF; $V_{CC(A)} = 1.4 \text{ V to}$	1.6 V								
t _{pd}	propagation delay	A to Y; see Figure 7	[2]							
		V _{CC(Y)} = 1.1 V to 1.3 V		2.8	10.8	27.1	2.6	27.7	27.7	ns
		$V_{CC(Y)} = 1.4 \text{ V to } 1.6 \text{ V}$		2.8	7.6	15.7	2.4	17.0	17.6	ns
		$V_{CC(Y)} = 1.65 \text{ V to } 1.95 \text{ V}$		2.5	6.3	12.3	2.4	13.5	14.1	ns
		$V_{CC(Y)} = 2.3 \text{ V to } 2.7 \text{ V}$		2.3	5.3	9.2	2.4	9.9	10.3	ns
		$V_{CC(Y)} = 3.0 \text{ V to } 3.6 \text{ V}$		2.6	4.9	7.8	2.3	8.3	8.7	ns
C _L = 15	pF; V _{CC(A)} = 1.65 V t	o 1.95 V								
t _{pd}	propagation delay	A to Y; see Figure 7	[2]							
		$V_{CC(Y)} = 1.1 \text{ V to } 1.3 \text{ V}$		2.7	10.5	26.4	2.5	27.1	27.3	ns
		V _{CC(Y)} = 1.4 V to 1.6 V		2.7	7.2	15.0	2.3	16.4	17.0	ns
	V _{CC(Y)} = 1.65 V to 1.95 V		2.4	6.0	11.7	2.3	12.8	13.5	ns	
		$V_{CC(Y)} = 2.3 \text{ V to } 2.7 \text{ V}$		2.2	4.9	8.5	2.2	9.2	9.7	ns
		$V_{CC(Y)} = 3.0 \text{ V to } 3.6 \text{ V}$		2.5	4.5	7.1	2.2	7.7	8.0	ns
C _L = 15	pF; V _{CC(A)} = 2.3 V to	2.7 V								
t _{pd}	propagation delay	A to Y; see Figure 7	[2]							
		$V_{CC(Y)} = 1.1 \text{ V to } 1.3 \text{ V}$		2.6	10.1	26.0	2.4	26.7	26.7	ns
		$V_{CC(Y)} = 1.4 \text{ V to } 1.6 \text{ V}$		2.7	6.9	14.3	2.3	15.7	16.3	ns
		V _{CC(Y)} = 1.65 V to 1.95 V		2.4	5.6	10.9	2.2	12.1	12.7	ns
		$V_{CC(Y)} = 2.3 \text{ V to } 2.7 \text{ V}$		2.1	4.5	7.6	2.2	8.4	8.9	ns
		$V_{CC(Y)} = 3.0 \text{ V to } 3.6 \text{ V}$		2.4	4.1	6.2	2.1	6.8	7.2	ns
C _L = 15	pF; V _{CC(A)} = 3.0 V to	3.6 V								
t _{pd}	propagation delay		[2]							
		V _{CC(Y)} = 1.1 V to 1.3 V		2.6	9.8	25.7	2.4	26.2	26.2	ns
		$V_{CC(Y)} = 1.4 \text{ V to } 1.6 \text{ V}$		2.7	6.6	14.0	2.3	15.2	15.7	ns
		$V_{CC(Y)} = 1.65 \text{ V to } 1.95 \text{ V}$		2.4	5.4	10.5	2.2	11.6	12.1	ns
		$V_{CC(Y)} = 2.3 \text{ V to } 2.7 \text{ V}$		2.1	4.3	7.3	2.2	7.9	8.4	ns
		$V_{CC(Y)} = 3.0 \text{ V to } 3.6 \text{ V}$		2.4	3.9	5.9	2.1	6.4	6.8	ns

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Product data sheet

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Low-power dual supply translating buffer

Table 8. Dynamic characteristics ...continued

Voltages are referenced to GND (ground = 0 V); for test circuit see <u>Figure 8</u>.

Symbol	Parameter	Conditions		25 °		5 °C		-40 °C to +125 °C		Unit
				Min	Typ[1]	Max	Min	Max (85 °C)	Max (125 °C)	
$C_{L} = 30 \mu$	oF; V _{CC(A)} = 1.1 V to	1.3 V			'	'				
t _{pd}	propagation delay	A to Y; see Figure 7	[2]							
		$V_{CC(Y)} = 1.1 \text{ V to } 1.3 \text{ V}$		3.7	13.7	32.9	3.5	33.5	33.5	ns
		$V_{CC(Y)} = 1.4 \text{ V to } 1.6 \text{ V}$		3.6	9.8	19.5	3.6	20.9	21.4	ns
		$V_{CC(Y)} = 1.65 \text{ V to } 1.95 \text{ V}$		3.7	8.4	15.9	3.5	17.0	17.7	ns
		$V_{CC(Y)} = 2.3 \text{ V to } 2.7 \text{ V}$		3.0	7.2	12.2	3.4	12.7	13.2	ns
		$V_{CC(Y)} = 3.0 \text{ V to } 3.6 \text{ V}$		3.8	6.8	10.9	3.4	12.2	12.5	ns
$C_L = 30 \mu$	oF; V _{CC(A)} = 1.4 V to	1.6 V								
t _{pd}	propagation delay	A to Y; see Figure 7	[2]							
		V _{CC(Y)} = 1.1 V to 1.3 V		3.5	13.1	31.5	3.2	32.0	32.0	ns
		V _{CC(Y)} = 1.4 V to 1.6 V		3.3	9.1	17.8	3.3	19.2	19.9	ns
		$V_{CC(Y)} = 1.65 \text{ V to } 1.95 \text{ V}$		3.4	7.6	14.2	3.2	15.4	16.0	ns
		$V_{CC(Y)} = 2.3 \text{ V to } 2.7 \text{ V}$		2.8	6.4	10.3	3.1	11.0	11.5	ns
		$V_{CC(Y)} = 3.0 \text{ V to } 3.6 \text{ V}$		3.5	5.9	8.9	3.1	10.1	10.5	ns
$C_{L} = 30 \text{ p}$	oF; V _{CC(A)} = 1.65 V t	o 1.95 V								
t _{pd}	propagation delay	A to Y; see Figure 7	[2]							
		V _{CC(Y)} = 1.1 V to 1.3 V		3.4	12.7	30.7	3.1	31.5	31.5	ns
		$V_{CC(Y)} = 1.4 \text{ V to } 1.6 \text{ V}$		3.2	8.8	17.2	3.2	18.7	19.3	ns
		$V_{CC(Y)} = 1.65 \text{ V to } 1.95 \text{ V}$		3.3	7.3	13.5	3.1	14.7	15.4	ns
		$V_{CC(Y)} = 2.3 \text{ V to } 2.7 \text{ V}$		2.7	6.0	9.6	3.0	10.4	10.9	ns
		$V_{CC(Y)} = 3.0 \text{ V to } 3.6 \text{ V}$		3.4	5.6	8.2	2.9	9.4	9.8	ns
$C_{L} = 30 \text{ p}$	oF; V _{CC(A)} = 2.3 V to	2.7 V								
t _{pd}	propagation delay	A to Y; see Figure 7	[2]							
		V _{CC(Y)} = 1.1 V to 1.3 V		3.3	12.4	30.3	3.1	31.0	31.0	ns
		$V_{CC(Y)} = 1.4 \text{ V to } 1.6 \text{ V}$		3.2	8.4	16.5	3.1	18.0	18.7	ns
		$V_{CC(Y)} = 1.65 \text{ V to } 1.95 \text{ V}$		3.2	6.9	12.8	3.0	14.0	14.6	ns
		$V_{CC(Y)} = 2.3 \text{ V to } 2.7 \text{ V}$		2.6	5.6	8.8	2.9	9.6	10.1	ns
		$V_{CC(Y)} = 3.0 \text{ V to } 3.6 \text{ V}$		3.3	5.2	7.3	2.9	8.5	9.0	ns
$C_{L} = 30 \text{ p}$	oF; $V_{CC(A)} = 3.0 \text{ V to}$	3.6 V								
t _{pd}	propagation delay	A to Y; see Figure 7	[2]							
		$V_{CC(Y)} = 1.1 \text{ V to } 1.3 \text{ V}$		3.3	12.0	30.0	3.1	30.5	30.5	ns
		$V_{CC(Y)} = 1.4 \text{ V to } 1.6 \text{ V}$		3.2	8.1	16.2	3.1	17.5	18.1	ns
		$V_{CC(Y)} = 1.65 \text{ V to } 1.95 \text{ V}$		3.2	6.7	12.4	3.0	13.4	14.1	ns
		$V_{CC(Y)} = 2.3 \text{ V to } 2.7 \text{ V}$		2.6	5.5	8.5	2.9	9.1	9.6	ns
		$V_{CC(Y)} = 3.0 \text{ V to } 3.6 \text{ V}$		3.2	5.0	7.0	2.9	8.1	8.5	ns

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Table 8. Dynamic characteristics ... continued

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 8.

Symbol	Parameter	Conditions		25 °C		-40 °C to +125 °C			Unit	
					Typ[1]	Max	Min	Max (85 °C)	Max (125 °C)	
$C_L = 5 pl$	F, 10 pF, 15 pF and	30 pF								
C _{PD} power dissipar capacitance	power dissipation	$f_i = 1 \text{ MHz}; V_I = \text{GND to } V_{CC(A)}$	[3][4]							
	capacitance	$V_{CC(A)} = V_{CC(Y)} = 1.2 \text{ V}$		-	3.8	-	-	-	-	pF
		$V_{CC(A)} = V_{CC(Y)} = 1.5 \text{ V}$		-	3.8	-	-	-	-	pF
		$V_{CC(A)} = V_{CC(Y)} = 1.8 \text{ V}$		-	4.1	-	-	-	-	pF
		$V_{CC(A)} = V_{CC(Y)} = 2.5 \text{ V}$		-	4.2	-	-	-	-	pF
		$V_{CC(A)} = V_{CC(Y)} = 3.3 \text{ V}$		-	4.6	-	-	-	-	pF

- [1] All typical values are measured at nominal V_{CC}.
- [2] t_{pd} is the same as t_{PLH} and t_{PHL} .
- [3] All specified values are the average typical values over all stated loads.
- [4] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

$$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma (C_L \times V_{CC}^2 \times f_o)$$
 where:

 f_i = input frequency in MHz;

f_o = output frequency in MHz;

C_L = output load capacitance in pF;

V_{CC} = supply voltage in V;

N = number of inputs switching;

 $\Sigma (C_L \times V_{CC}{}^2 \times f_{\text{o}})$ = sum of the outputs.

12. Waveforms

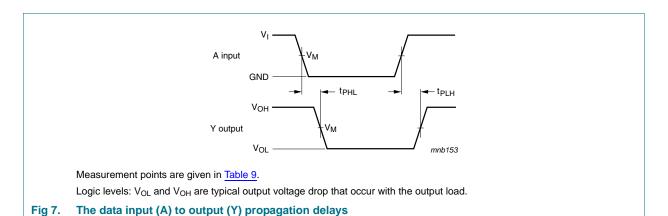


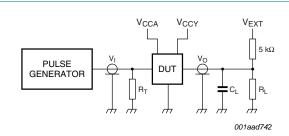
Table 9. Measurement points

Supply voltage	Output	Input				
V _{CC(A)} /V _{CC(Y)}	V _M	V _M	V _I	$t_r = t_f$		
1.1 V to 3.6 V	$0.5 \times V_{CC(Y)}$	$0.5 \times V_{CC(A)}$	$V_{CC(A)}$	≤ 3.0 ns		

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Test data is given in Table 10.

Definitions for test circuit:

R_L = Load resistance.

 C_L = Load capacitance including jig and probe capacitance.

 R_T = Termination resistance should be equal to the output impedance Z_0 of the pulse generator.

 V_{EXT} = External voltage for measuring switching times.

Fig 8. Test circuit for measuring switching times

Table 10. Test data

Supply voltage	Load	V _{EXT}	
V _{CC(A)} /V _{CC(Y)}	C _L	R _L [1]	t _{PLH} , t _{PHL}
1.1 V to 3.6 V	5 pF, 10 pF, 15 pF and 30 pF	5 k Ω or 1 M Ω	open

[1] For measuring enable and disable times R_L = 5 $k\Omega$, for measuring propagation delays, setup and hold times and pulse width R_L = 1 $M\Omega$.

13. Package outline

TSSOP5: plastic thin shrink small outline package; 5 leads; body width 1.25 mm

SOT353-1

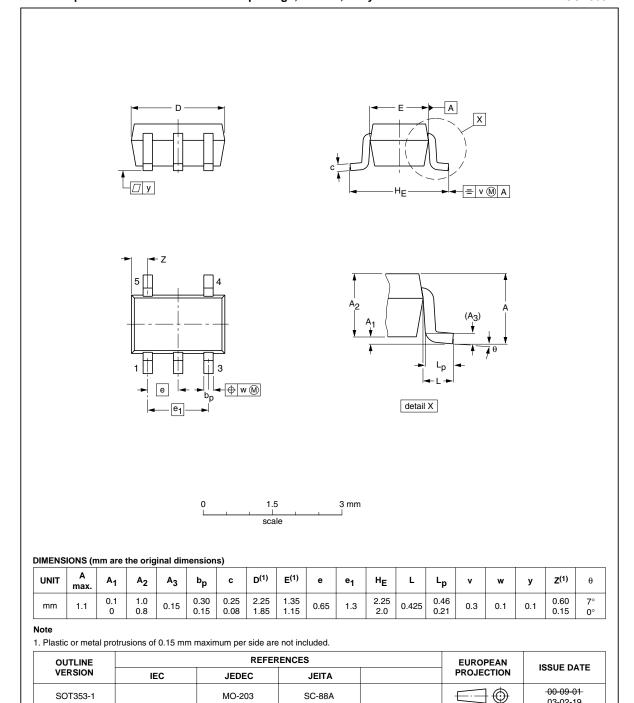


Fig 9. Package outline SOT353-1 (TSSOP5)

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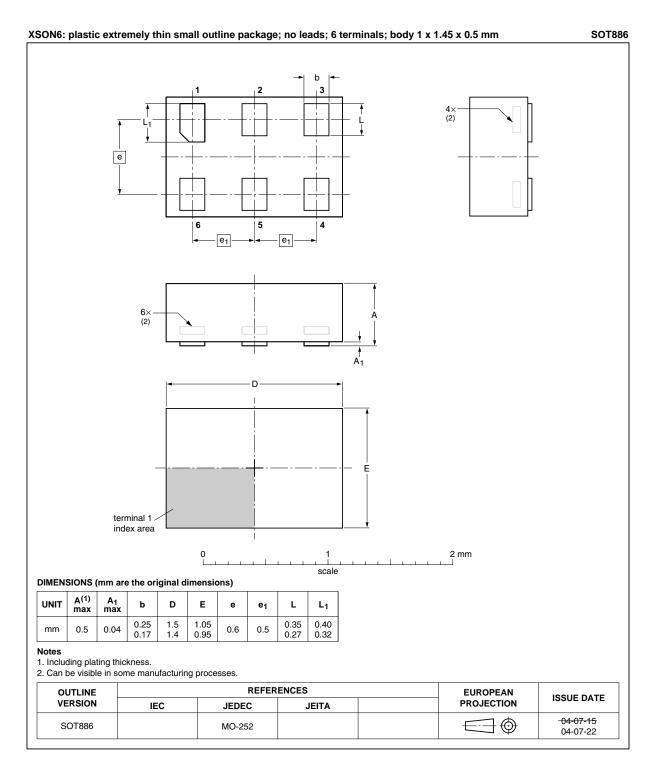


Fig 10. Package outline SOT886 (XSON6)

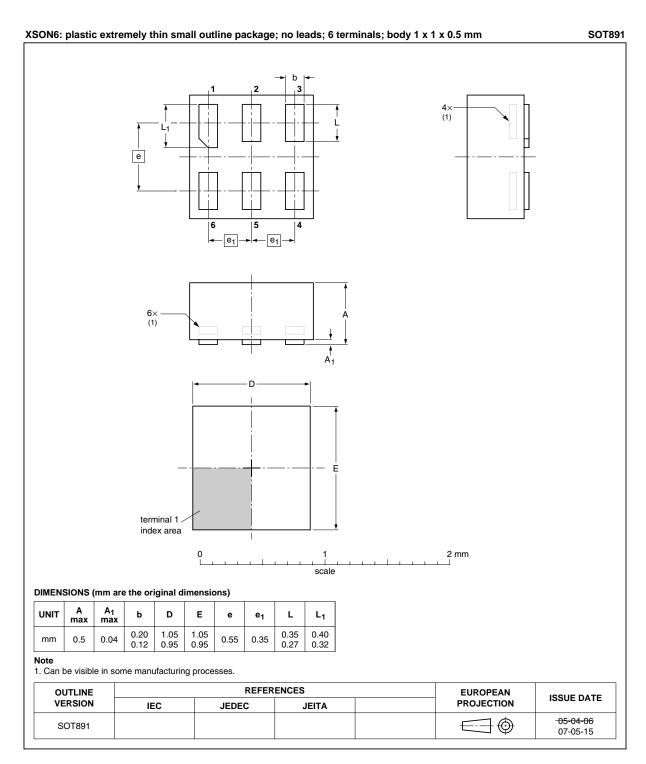


Fig 11. Package outline SOT891 (XSON6)

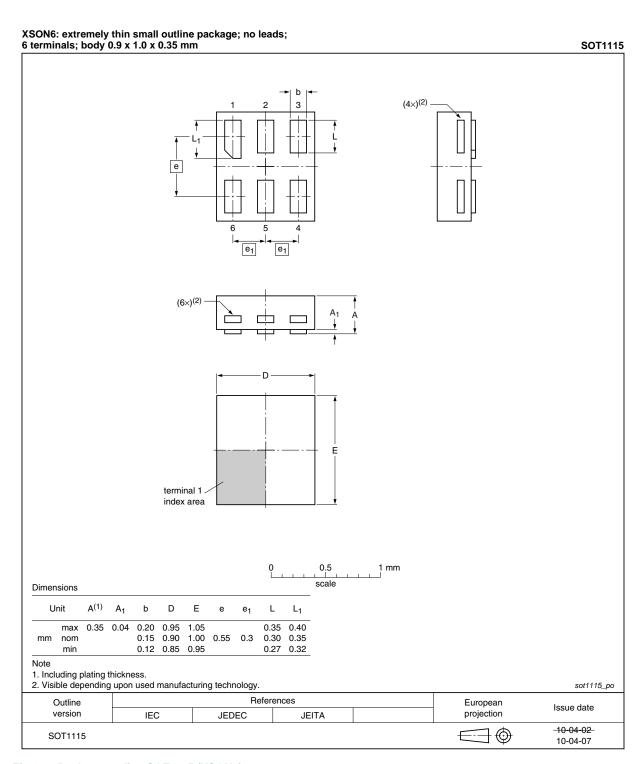


Fig 12. Package outline SOT1115 (XSON6)

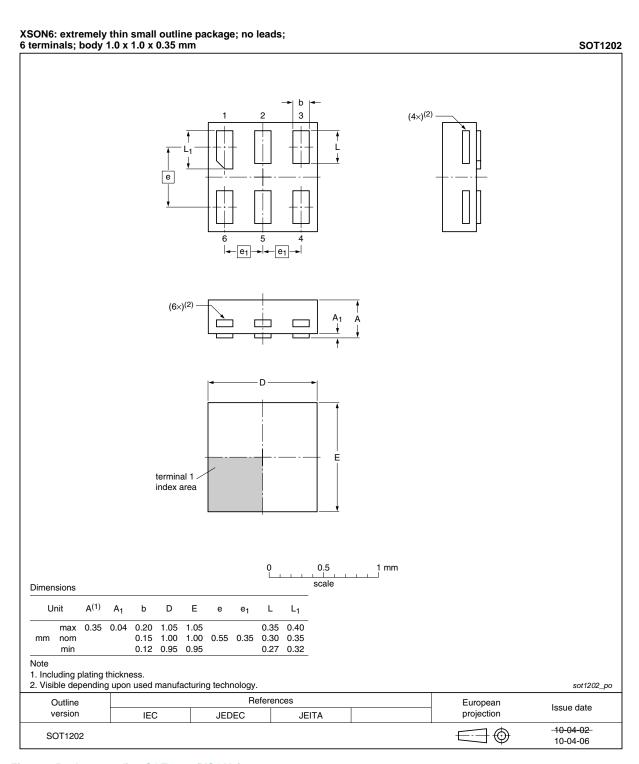


Fig 13. Package outline SOT1202 (XSON6)

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14. Abbreviations

Table 11. Abbreviations

Acronym	Description
CDM	Charged Device Model
DUT	Device Under Test
ESD	ElectroStatic Discharge
НВМ	Human Body Model
MM	Machine Model

15. Revision history

Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74AUP1T34 v.2	20100819	Product data sheet	-	74AUP1T34 v.1
Modifications:	 Added type r 	number 74AUP1T34GN (SOT	1115/XSON6 package)	
	 Added type r 	number 74AUP1T34GS (SOT1	1202/XSON6 package)	
74AUP1T34 v.1	20061204	Product data sheet	-	-

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16. Legal information

16.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions"
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